Electronic Supplementary Information

A versatile molecular logic system based on Eu(III) coordination

polymer film electrodes combined with multiple properties of NADH

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3.1 Characterization of Eu(III)-PMAG films



Fig. S1 CVs of 0.5 mM FcDA at 0.05 V s⁻¹ in pH 5.0 buffers at (a) ITO and (b) Eu(III)-

PMAG film electrodes.



Fig. S2 FTIR spectra of (a) MAG, (b) PMAG and (c) Eu(III)-PMAG samples.



Fig. S3 (A) FL emission spectra for (a) bare ITO, (b) dry PMAG films, (c) dry Eu(III)-PMAG films and (d) Eu(III)-PMAG films in pH 5.0 buffers. (B) Dependence of the FL_{617} intensity for Eu(III)-PMAG films upon immersion time in pH 5.0 buffers.



Fig. S4 (A) FL spectra of (a) dry Eu(III)-PMAG films and Eu(III)-PMAG films in buffers at pH (b) 6.0, (c) 5.0, (d) 4.0 and (e) 3.0. (B) Dependence of the FL_{617} intensity for Eu(III)-PMAG films upon different pHs.

3.2 Cu(II)-sensitive FL for Eu(III)-PMAG films

Compared with the Eu(III)-PMAG film electrodes before the immersion in Cu(II) solution (Fig. S5A, curve a), an obvious Cu2p_{3/2} XPS peak was observed after the immersion of the film electrodes in 5 mM Cu(II) solution (Fig. S5A, curve b), indicating that Cu(II) indeed coordinated with PMAG films. Moreover, the average binding energy of Cu2p_{3/2} for the Eu(III)-PMAG samples after the interaction with Cu(II) (933.32 eV) reduced by 0.93 eV compared with the copper acetate powder sample (934.25 eV) (Fig. S5A, curve c). At the same time, the average binding energy of Eu3d_{5/2} in Eu(III)-PMAG sample (1135.42 eV) increased by 0.87 eV after the immersion in the Cu(II) solution (1136.29 eV) (Fig. S5B). These results suggested that the coordination of Cu(II) with the N and O atoms of PMAG in the films increased the electron density of Cu(II). In addition, the coordination of Cu(II) with PMAG affected the coordination action of Eu(III) ions, which changed the coordination environment around Eu(III) and PMAG and reduced the electron density of Eu(III). All of these supported that Cu(II) could coordinate with PMAG films and further affect the luminescent behavior of Eu(III)-PMAG films.



Fig. S5 (A) XPS spectra of $Cu2p_{3/2}$ for Eu(III)-PMAG film electrodes (a) before and (b) after immersing in pH 5.0 solution containing 5.0 mM Cu(II), and (c) $Cu(CH_3COO)_2 \cdot H_2O$ powder. (B) XPS spectra of Eu3d_{5/2} for Eu(III)-PMAG film electrodes (a) before and (b) after immersing in pH 5.0 solution containing 5.0 mM Cu(II).



Fig. S6 (A) Dependence of the FL_{617} for Eu(III)-PMAG films after immersion in pH 5.0 buffers containing 5.0 mM Cu(II) upon different EDTA concentrations. (B) Dependence of the FL_{617} for Eu(III)-PMAG films upon immersion time in pH 5.0 buffers containing 8.0 mM EDTA.



Fig. S7 (A) UV-vis absorption spectra for Eu(III)-PMAG films in pH 5.0 buffers containing (a) 0, (b) 5.0 mM and (c) 5.0 mM Cu(II) + 8.0 mM EDTA. (B) Dependence of the A_{733} for Eu(III)-PMAG films after immersion in pH 5.0 buffers containing 5.0 mM Cu(II) upon different EDTA concentrations (c_{EDTA}).

3.3 NADH-sensitive FL for Eu(III)-PMAG films



Fig. S8 (A) UV-vis absorption spectra of (a) 0.5, (b) 1.0 and (c) 5.0 mM NADH in pH 5.0 buffers. (B) Fluorescence (a) excitation and (b) emission spectra ($\lambda_{ex} = 396$ nm) of 5.0 mM NADH in pH 5.0 buffers.



Fig. S9 Variation of (A) FL_{617} and (B) FL_{468} for Eu(III)-PMAG films in pH 5.0 buffers with the NADH concentration switched between 0 and 5.0 mM.

3.5 Establishment of a 4-input/10-output logic gate

| Input A (Cu(II)) | Input B (EDTA) | Input C (NADH) | Input D (FcDA) | Output FL ₁ | Output FL ₂ | Output FL ₃ | Output FL ₄ | Output IP ₁ | Output IP ₂ | Output IP ₃ | Output AB ₁ | Output AB ₂ | Output AB ₃ |
|---------------------|-------------------|-------------------|-------------------|---------------------------|---------------------------|---------------------------|---------------------------|---------------------------|---------------------------|---------------------------|---------------------------|---------------------------|---------------------------|
| 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 1 |
| 1 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 1 | 0 |
| 0 | 1 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 1 |
| 1 | 1 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 | 0 |
| 0 | 0 | 1 | 0 | 0 | 0 | 1 | 1 | 0 | 0 | 1 | 0 | 0 | 1 |
| 1 | 0 | 1 | 0 | 0 | 0 | 1 | 1 | 0 | 0 | 1 | 0 | 1 | 0 |
| 0 | 1 | 1 | 0 | 0 | 0 | 1 | 1 | 0 | 0 | 1 | 0 | 0 | 1 |
| 1 | 1 | 1 | 0 | 0 | 0 | 1 | 1 | 0 | 0 | 1 | 1 | 0 | 0 |
| 0 | 0 | 0 | 1 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 1 |
| 1 | 0 | 0 | 1 | 0 | 1 | 0 | 0 | 0 | 1 | 0 | 0 | 1 | 0 |
| 0 | 1 | 0 | 1 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 1 |
| 1 | 1 | 0 | 1 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 1 | 0 | 0 |
| 0 | 0 | 1 | 1 | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 0 | 0 | 1 |
| 1 | 0 | 1 | 1 | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 0 | 1 | 0 |
| 0 | 1 | 1 | 1 | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 0 | 0 | 1 |
| 1 | 1 | 1 | 1 | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 1 | 0 | 0 |

 Table S1 Truth table of the 4-input/10-output logic gate circuit

3.6 Establishment of an encoder, a decoder, a demultiplexer and a parity checker



Fig. S10 (A) Truth table and (B) logic symbol of a 2-to-1 encoder, employing NADH and Cu(II) as two inputs and FL_{468} (FL₄) as the output.



Fig. S11 (A) Truth table and (B) logic symbol of a 1-to-2 decoder, employing Cu(II) as the input and FL_{617} (FL₁) and A_{733} (AB₂) as outputs.

3.8 Fabrication of the dual transfer gate



Fig. S12 (A) Truth table and (B) symbolic representation of the dual transfer gate, employing Cu(II) and FcDA as inputs and FL_{617} (FL₂) and CV I_{pa} at 0.5 V (IP₂) as outputs.